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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
09/891,324	06/27/2001	Osamu Samuel Nakagawa	10004808-1	3635	
7:	590 05/24/2006		EXAMINER		
	ACKARD COMPA	SCHILLINGER, LAURA M			
Intellectual Property Administration P.O. Box 272400 Fort Collins, CO 80527-2400			· · · · · · · · · · · · · · · · · · ·	D. DED . V. U. (DED	
			ART UNIT	PAPER:NUMBER	
			2813		

DATE MAILED: 05/24/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

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		Application No.	Applicant(s)			
Office Action Summary		09/891,324	NAKAGAWA, OSA	MU SAMUEL		
		Examiner	Art Unit			
		Laura M. Schillinger	2813			
Period fo	The MAILING DATE of this communication app or Reply	pears on the cover sheet with the c	orrespondence add	iress		
A SHOWHIC - Exter after - If NO - Failu Any r	ORTENED STATUTORY PERIOD FOR REPLICHEVER IS LONGER, FROM THE MAILING DOTAINS IN THE MAILING DOTAINS IN THE MAILING DOTAINS IN THE MAILING DOTAINS IN THE MAILING T	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be tin will apply and will expire SIX (6) MONTHS from a cause the application to become ABANDONE	N. nely filed the mailing date of this cor D (35 U.S.C. § 133).			
Status						
2a) <u></u>	Responsive to communication(s) filed on 14 N This action is FINAL . 2b) This Since this application is in condition for allowa closed in accordance with the practice under B	s action is non-final. nce except for formal matters, pro		merits is		
Dispositi	on of Claims					
5)□ 6)⊠ 7)□	Claim(s) 1-13 is/are pending in the application 4a) Of the above claim(s) is/are withdra Claim(s) is/are allowed. Claim(s) 1-13 is/are rejected. Claim(s) is/are objected to. Claim(s) are subject to restriction and/or	wn from consideration.				
Applicati	on Papers					
10)	The specification is objected to by the Examine The drawing(s) filed on is/are: a) acc Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct The oath or declaration is objected to by the Example 2.	cepted or b) objected to by the drawing(s) be held in abeyance. Settion is required if the drawing(s) is ob	e 37 CFR 1.85(a). jected to. See 37 CF			
Priority ι	ınder 35 U.S.C. § 119		•			
 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No. 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 						
2) Notic 3) Infor	t(s) e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO-1449 or PTO/SB/08) r No(s)/Mail Date	4) Interview Summary Paper No(s)/Mail D 5) Notice of Informal F 6) Other:	ate	1-152)		

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DETAILED ACTION

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1-13 are rejected under 35 U.S.C. 102(b) as being anticipated by Sandhu ('206).

In reference to claim 1, Sandhu teaches a method comprising:

Forming a first electrode (20) in a first dielectric layer (18 or 19) of the multi-level metallization device (Fig.3B)

Depositing a substantially thin dielectric material layer (22) over the first dielectric layer (18 or 19) of the multi-level metallization device (herein after referred to as "MLM") (100) (Fig.3B); and

Forming a second electrode (25) in a second dielectric layer (23), wherein the second dielectric layer (23) is formed substantially over the substantially thin dielectric layer (22) (Fig.3B).

In reference to claim 2, Sandhu teaches further comprising:

Patterning the substantially thin dielectric material (22) to substantially cover the first electrode (20); and

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Adjusting the thickness of the thin dielectric material layer (Col.5, lines: 10-15-controlled deposition is adjusting the thickness; Col.6, lines: 5-15).

In reference to claim 3, Sandhu teaches wherein a dielectric constant of the substantially thin dielectric layer is substantially high (Col.6, lines: 15-45)).

In reference to claim 4, Sandhu teaches wherein the substantially thin dielectric layer includes SiN (Col.2, lines: 20-25).

In reference to claim 5, Sandhu teaches wherein the thickness of the dielectric layer is between 50 to 100 A- however does teach that the dielectric is thin (Col.6, lines: 5-15).

In reference to claim 6, Sandhu teaches wherein the dielectric constant is between 4 and 100 (Col.1, lines: 15-20).

In reference to claim 7, Sandhu teaches further comprising:

Depositing a second dielectric layer over the substantially thin dielectric layer (23); and Etching at least one via adaptive to receive the second electrode (Col.3, lines: 50-55).

In reference to claim 8, Sandhu teaches further comprising:

Polishing the second metal layer (Col.3, lines: 50-60).

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In reference to claim 9, Sandhu teaches wherein etching the first electrode in a first dielectric layer of the MLM ((Col.3, lines: 50-60).

In reference to claim 10, Sandhu teaches wherein the first electrode is formed in a parallel line configuration (Fig.3B)

In reference to claim 11, Sandhu teaches wherein the second electrode is formed in a parallel line configuration (Fig.3B)

In reference to claim 12, Sandhu teaches wherein the dielectric is a composite (Fig. 3B).

In reference to claim 13, Sandhu teaches wherein the composite comprises PZT and platinum (Col.7, lines: 1-10 and Col.1, lines:60-65).

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Laura M. Schillinger whose telephone number is (571) 272-1697. The examiner can normally be reached on M-T, R-F 7:00-5:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl W. Whitehead, Jr. can be reached on (571) 272-1702. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

05/22/06

Laura M Schillinger Primary Examiner

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